

TECHNICAL DATA SHEET

6 Lake Street, Lawrence, MA 01841 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803 Website: http://www.microsemi.com

SCHOTTKY BARRIER DIODES – LEADLESS PACKAGE FOR SURFACE MOUNT – METALLURGICALLY BONDED – DOUBLE PLUG CONSTRUCTION

Qualified per MIL-PRF-19500/444

1N5711UR 1N5712UR		857UR-1 858UR-1	CDLL28 CDLL57 CDLL57	11	CDL	L6263 L6857 L6858		QUALIFIED LEVELS JAN JANTX JANTXV
MAXIMUM RA	TING AT 25°C							
Dperating Femperature: Storage Temper Dperating Curre Derating: ELECTRICAI	-65°C rature: 5711 ent: 2810, 6857 all typ	* 1	pes :75m :150i :Dera	A dc @ mA dc ate to 0		60°C 10°C dc @ +150°C		
TYPE NUMBER	MINIMUM BEAKDOWN VOLTAAGE	MAXIMUM FORWARD VOLTAGE	MAXIMUM FORWARD VOLTAGE	MAXIMUM REVERSE LEAKAGE CURRENT I _R @ V _R		MAXIMUM CAPACITANCE @ VR = 0 VOLTS f = 1.0MHz CT	ESDS CLASS	FIGURE 1
	V _{вк} @ 10µА	V _F @ 1mA	V _F @ I _F	IR	@ V _R			FIGURE I
	V _{BR} @ 10µА VOLTS	V _F @ 1mA VOLTS	V _F @ I _F VOLTS @ mA	I _R nA	@ V _R VOLTS			HOULI
1N5711UR-1		-	VOLTS			Ст	1	
1N5711UR-1 1N5712UR-1	VOLTS	VOLTS	VOLTS @ mA	nA	VOLTS	C _T PICO FARADS	1	
	VOLTS 70	VOLTS 0.41	VOLTS @ mA 1.0 @ 15	nA 200	VOLTS 50	C _T PICO FARADS 2.0		
1N5712UR-1	VOLTS 70 20	VOLTS 0.41 0.41	VOLTS @ mA 1.0 @ 15 1.0 @ 35	nA 200 150	VOLTS 50 16	Ст РІСО FARADS 2.0 2.0	1	
1N5712UR-1 1N6857UR-1	VOLTS 70 20 20	VOLTS 0.41 0.41 0.35	VOLTS @ mA 1.0 @ 15 1.0 @ 35 0.75 @ 35 0.75 @ 35	nA 200 150 150	VOLTS 50 16 16	Ст РІСО FARADS 2.0 2.0 4.5	1 2	
1N5712UR-1 1N6857UR-1 1N6858UR-1	VOLTS 70 20 20 70	VOLTS 0.41 0.41 0.35 0.36	VOLTS @ mA 1.0 @ 15 1.0 @ 35 0.75 @ 35 0.65 @ 15	nA 200 150 150 200	VOLTS 50 16 16 50	Ст РІСО FARADS 2.0 2.0 4.5 4.5	1 2 2	
1N5712UR-1 1N6857UR-1 1N6858UR-1 CDLL2810	VOLTS 70 20 20 70 20 20 20 20 20	VOLTS 0.41 0.41 0.35 0.36 0.41	VOLTS @ mA 1.0 @ 15 1.0 @ 35 0.75 @ 35 0.65 @ 15 1.0 @ 35 1.0 @ 35	nA 200 150 200 100	VOLTS 50 16 16 50 15	С _т PICO FARADS 2.0 2.0 4.5 4.5 2.0	1 2 2 1	
1N5712UR-1 1N6857UR-1 1N6858UR-1 CDLL2810 CDLL5711	VOLTS 70 20 20 20 20 70 20 70 20 70 20 70	VOLTS 0.41 0.41 0.35 0.36 0.41	VOLTS @ mA 1.0 @ 15 1.0 @ 35 0.75 @ 35 0.65 @ 15 1.0 @ 35 1.0 @ 35	nA 200 150 200 100 200	VOLTS 50 16 16 50 15 50	Ст РІСО FARADS 2.0 2.0 4.5 4.5 2.0 2.0 2.0	1 2 2 1 1	
1N5712UR-1 1N6857UR-1 1N6858UR-1 CDLL2810 CDLL5711 CDLL5712	VOLTS 70 20 20 20 70 20 70 20 70 20 70 20 70 20	VOLTS 0.41 0.41 0.35 0.36 0.41 0.41	VOLTS @ mA 1.0 @ 15 1.0 @ 35 0.75 @ 35 0.65 @ 15 1.0 @ 35 1.0 @ 15 1.0 @ 35 1.0 @ 35	nA 200 150 200 100 200 150 200 150	VOLTS 50 16 50 15 50 16	Ст РІСО FARADS 2.0 2.0 4.5 4.5 2.0 2.0 2.0 2.0	1 2 2 1 1 1 1	

- 1. Effective Minority Carrier Lifetime (τ) is 100 Pico Seconds
- 2. Qualification testing to J, JX, JV and JS levels for 6857 and 6858 types is underway. Contact the factory for qualification completion dates. These two part numbers are being introduced by CDI as "drop-in" replacements for the 5711 and 5712. They provide a more robust mechanical design and a higher ESDS class with the only trade-off being an increase in capacitance.

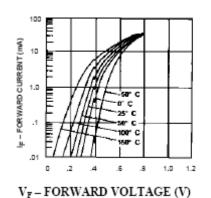


TECHNICAL DATA SHEET

GRAPHS

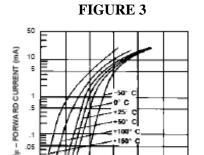
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FIGURE 1



I - V Curve Showing Typical Forward Voltage Variation with Temperature for the CDLL2810 and CDLL5712 Schottky

Diodes.



.6 .8 1.0 1.2

VF - FORWARD VOLTAGE (V)

I - V Curve Showing Typical Forward Voltage Variation with Temperature for Schottky Diode CDLL5711.

.2 .4

.01 0

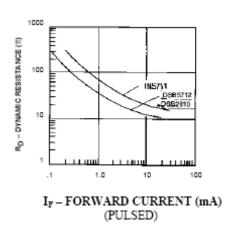
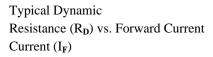
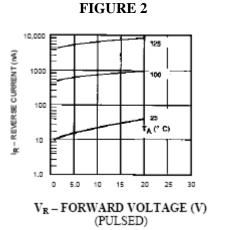
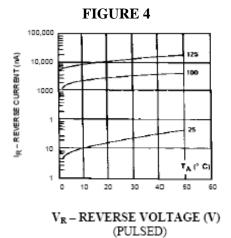


FIGURE 5





CDLL2810 and CDLL5712 Typical Variation of Reverse Current (I_R) vs. Reverse Voltage (V_R) at Various Temperatures



CDLL5711 Typical; Variation of Reverse Current (I_R); vs. ReverseVoltage (V_R) at Various Temperatures.

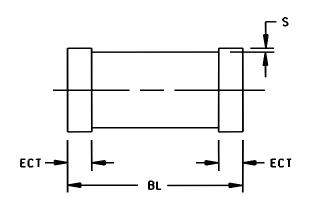
T4-LDS-0041 Rev. 1 (100246)

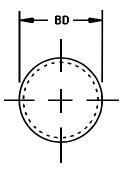


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PACKAGE DIMENSIONS





NOTE:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- 2. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

Symbol	Inc	hes	Millir	Notes		
	Min	Max	Min	Max		
BD	.063	.067	1.60	1.70		
BL	.130	.146	3.30	3.71		
ECT	.016	.022	0.41	0.55		
S	.001	Min				

DESIGN DATA

CASE: DO-213AA, Hermetically sealed glass case. (MELF, SOD-80, LL34)

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: ($R_{\theta JEC}$): 100°C/W maximum at L = 0 inch

THERMAL IMPEDANCE: (Z_{0JX}): 40°C/W maximum.

POLARITY: Cathode end is banded.

MOUNTING POSITION SURFACE SELECTION: The Axial Coefficient of Expansion (COE) of this device is approximately +6PPM/°C. The COE of the Mounting Surface System should be selected to provide a suitable match with this device.

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